University at Buffalo The State University of New York

IEEE MDTS conference 05/19/2025

Location-Controlled Chemical Vapor Deposition of MoS_2 for High-Performance Field-Effect Transistor Arrays

Presenter:

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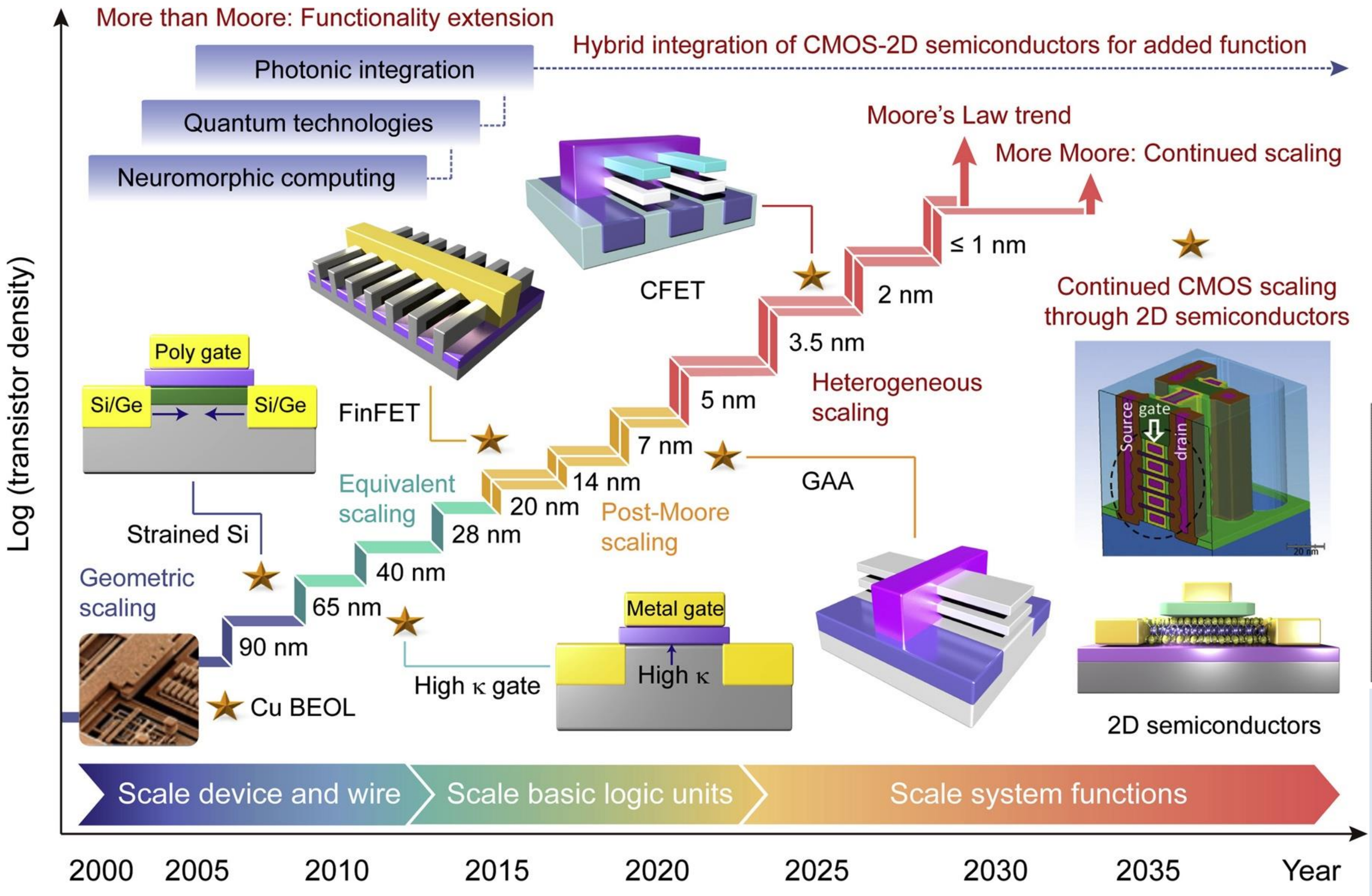
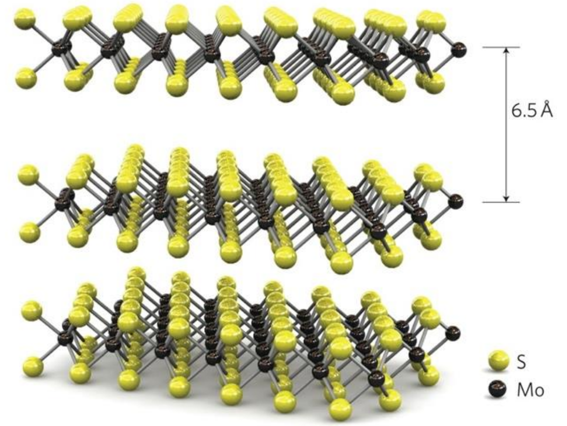
Paper Id: 28

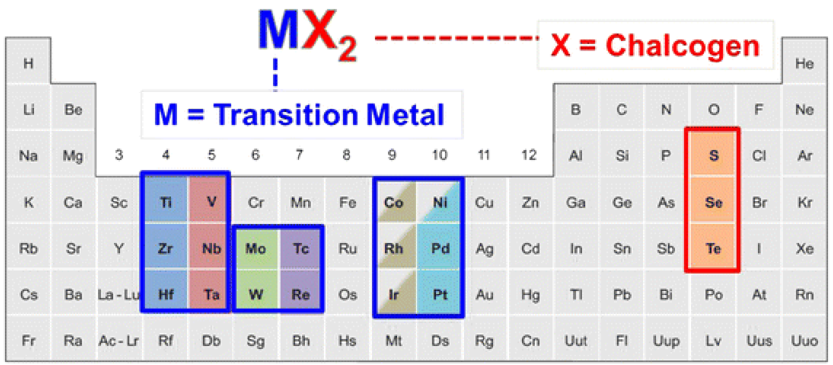
Presentation Time: SS1_4 12:35 pm – 12:55 pm

The rise of 2D TMDs

<u>Introductions</u> | Materials and methods | Results and discussion | Conclusion and highlights







- Two-dimensional (2D) transition metal dichalcogenides (TMDs) have been extensively explored as channel materials for electronic devices.

1. iScience Volume 25, Issue 10, 21 October 2022, 105160
2. Nature Nanotechnology volume 6, pages 147–150 (2011)
3. Nano Convergence volume 2, Article number: 17 (2015)

Site-specific synthesis

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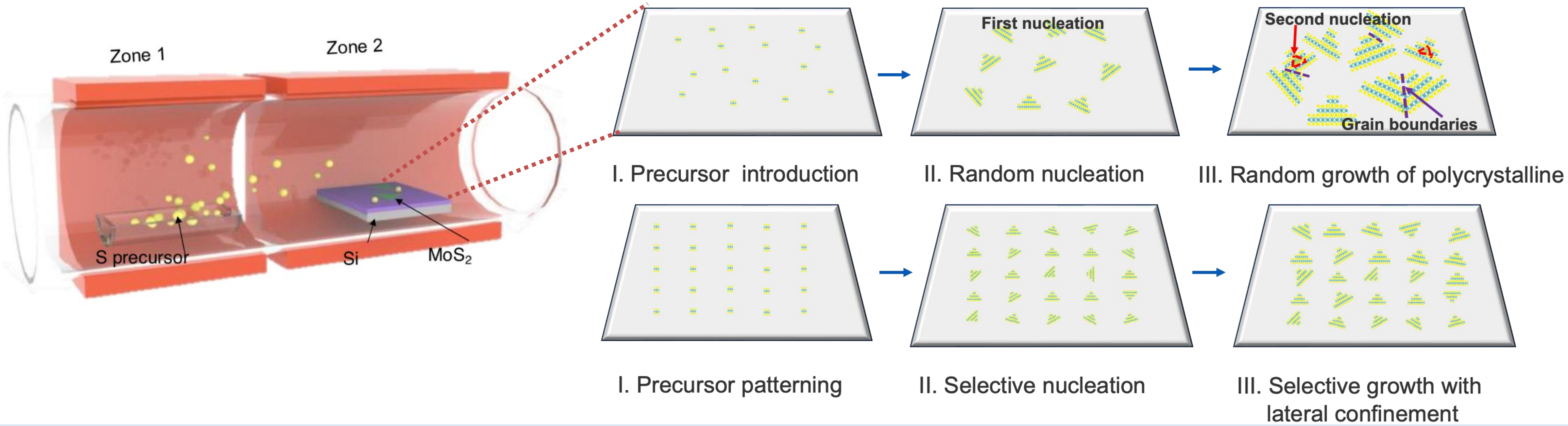
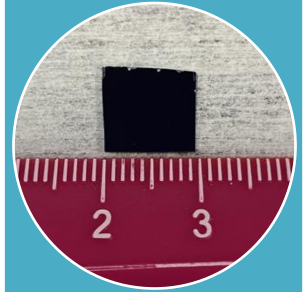


➢ **Challenges for nanoelectronics:**
Despite initial achievements in fundamental scientific research and device demonstrations, the growth of wafer-scale, single crystalline (SC) TMD films is a major obstacle to the advancement of commercially feasible TMD-based nanoelectronics.

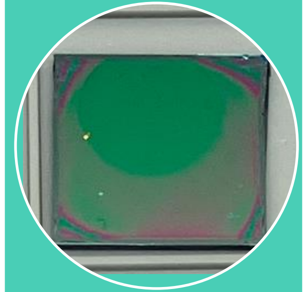
➢ **Solutions:**
Site-specific growth → allows micrometer scale controlled growth at selected locations which can be directly used as channel material for electronic devices.

1. Nature 614, 88–94 (2023)

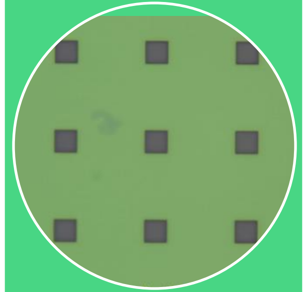
Experiment process



Substrate preparation



E-beam resists spin coating



E-beam lithography patterning

Mo precursor loading

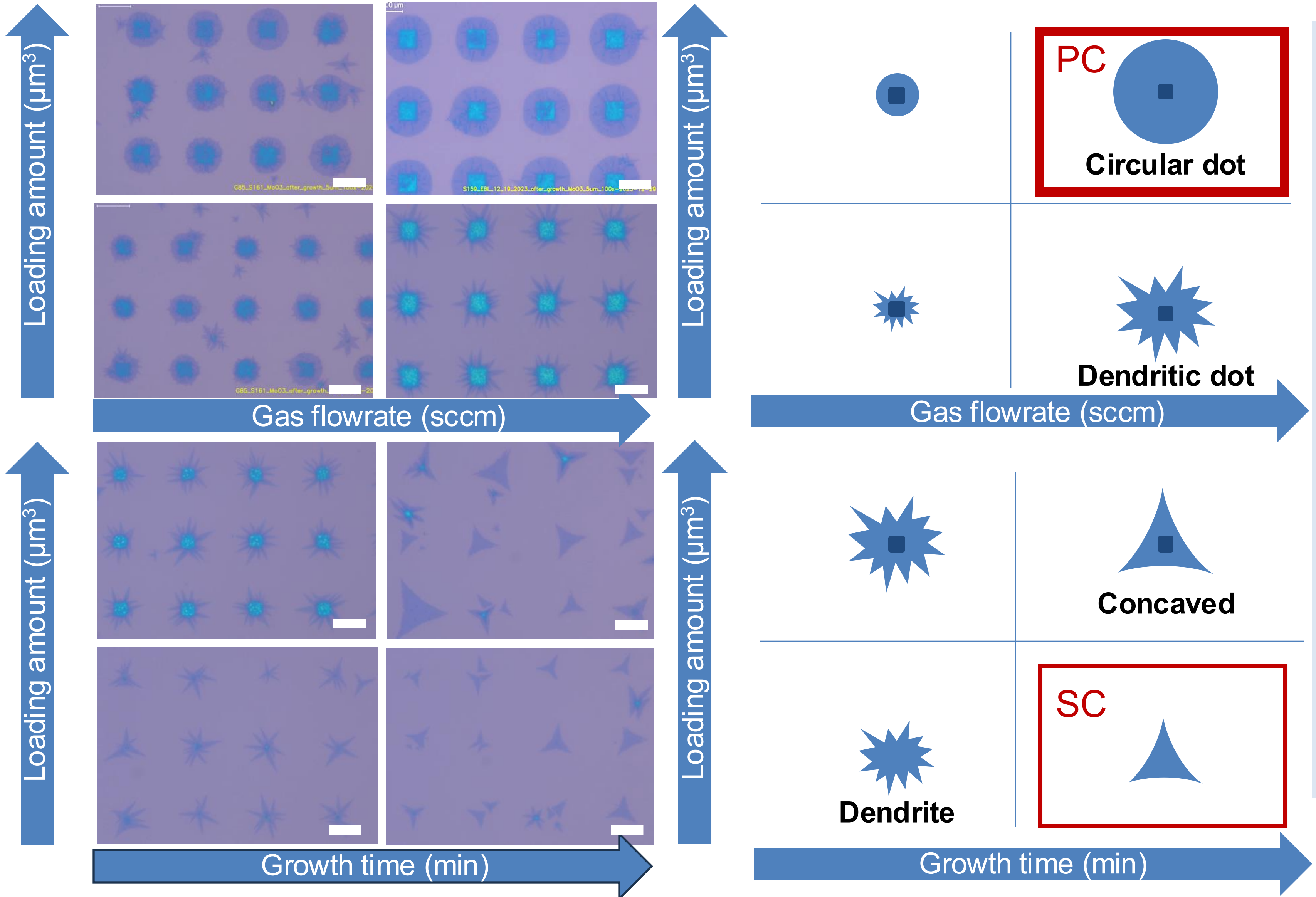
Acetone liftoff E-beam resists

Selective MoS_2 CVD synthesis

Materials Characterization

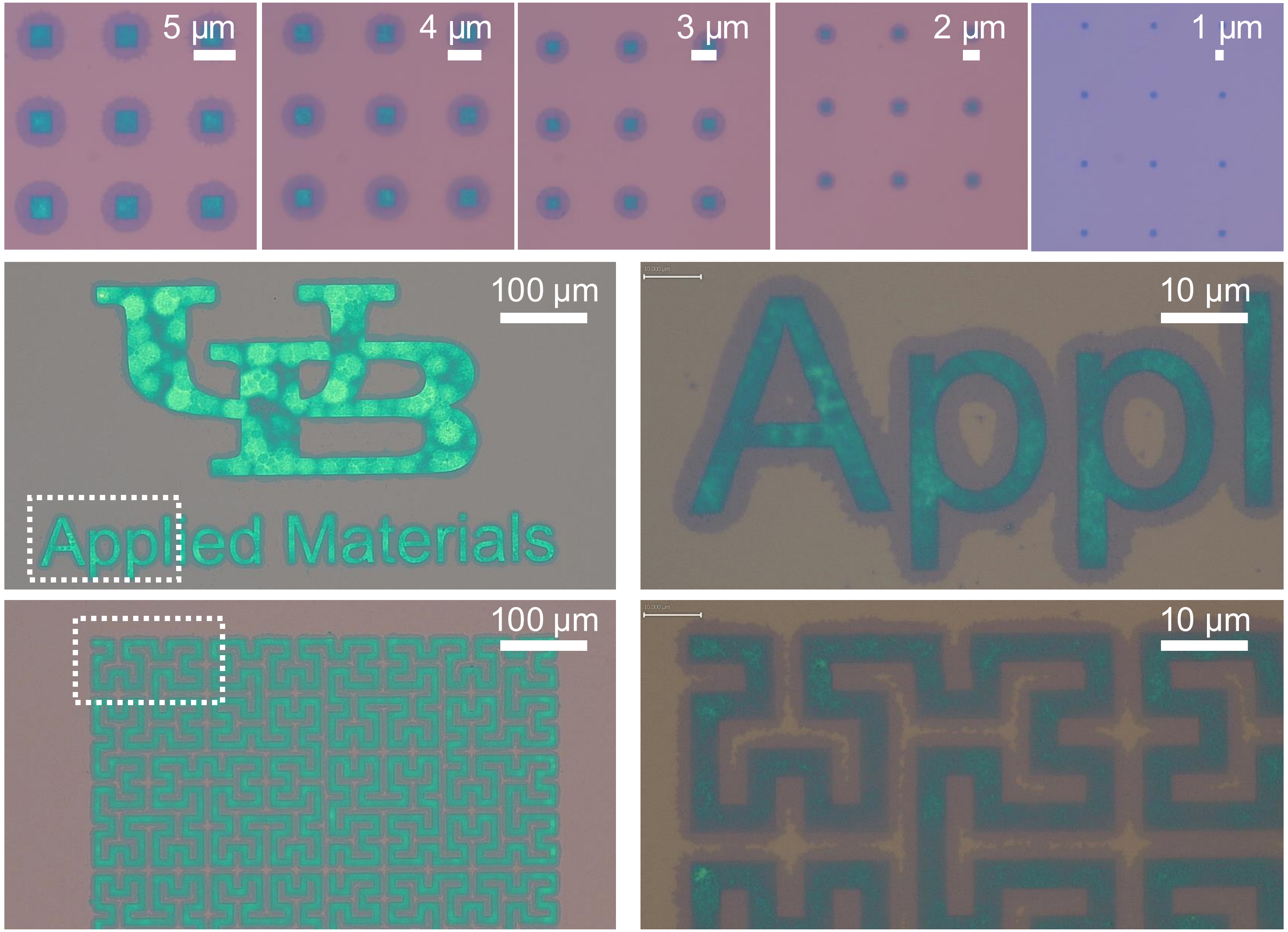
Device fabrication and performance measurement

CVD parameter space exploration



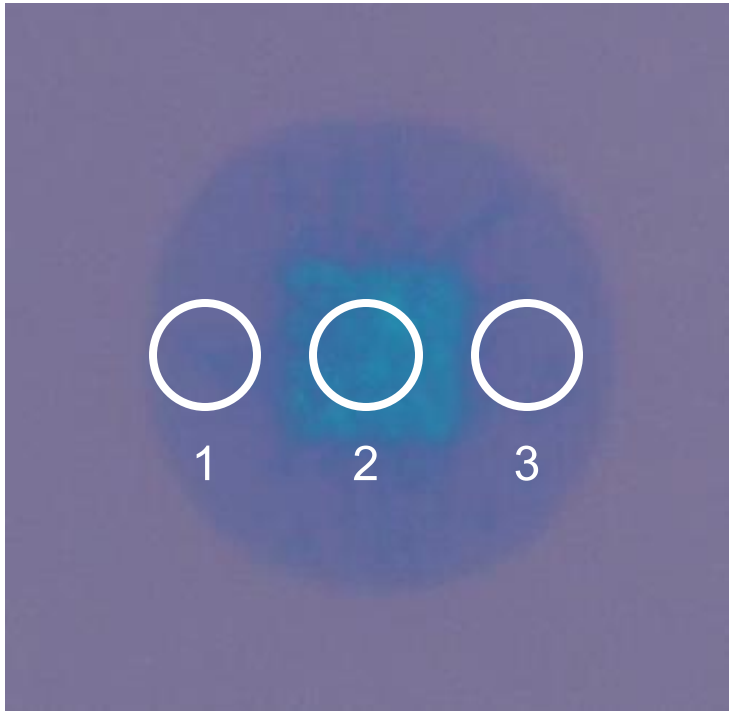
- Location-specific polycrystalline (PC) and single-crystalline (SC) flakes can be obtained by adjusting the CVD synthesis parameters.
- The electrical properties of monolayer MoS_2 were measured, demonstrating competitive performance compared to published results, though the recipe for equilateral triangle monolayers requires further refinement.
- In contrast, the recipe for circular dots is well-optimized and promising for further investigation.

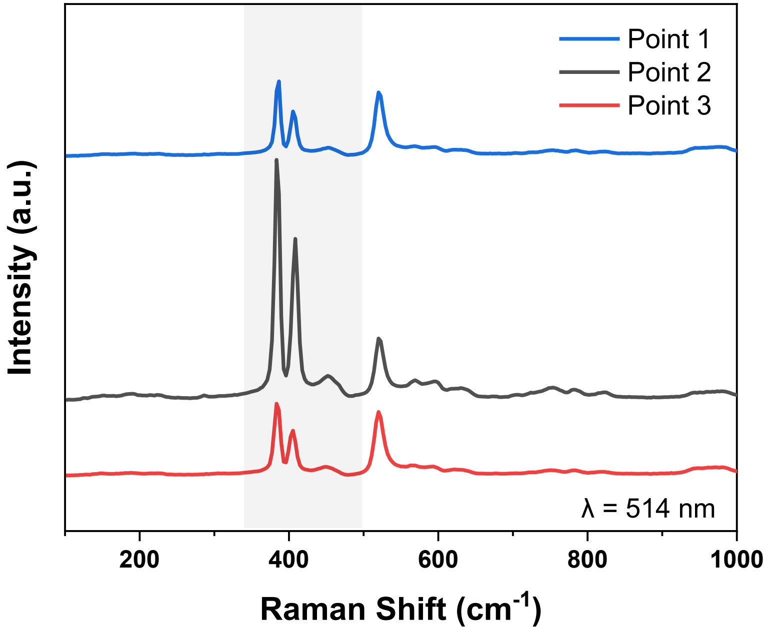
Location and size controlled MoS_2 synthesis

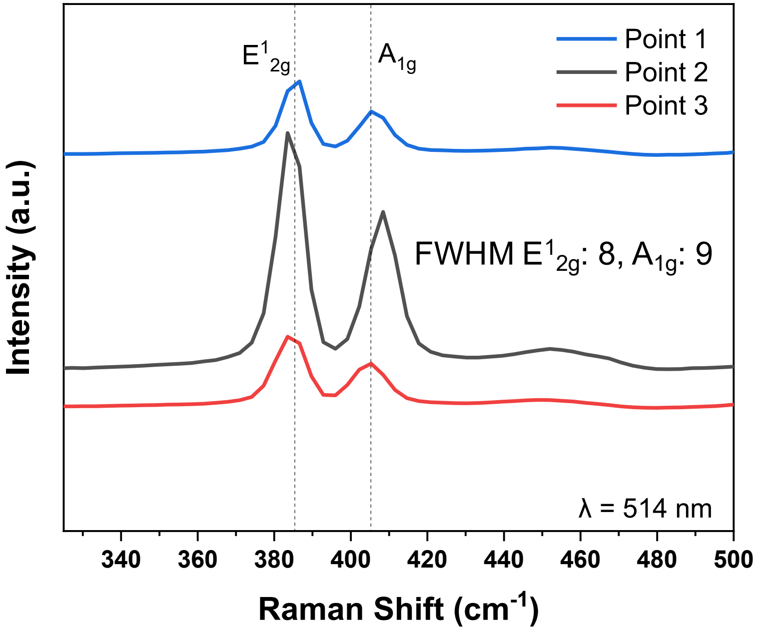


- MoS_2 flake size and location were precisely controlled by tuning CVD parameters and predefined MoO_3 deposition.
- Complex patterns, including "UB", "Applied Materials" logos, and Hilbert curves, were successfully synthesized.

Material characterization - Raman spectroscopy



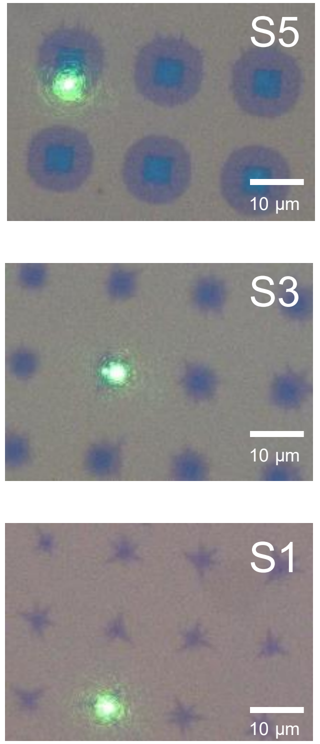


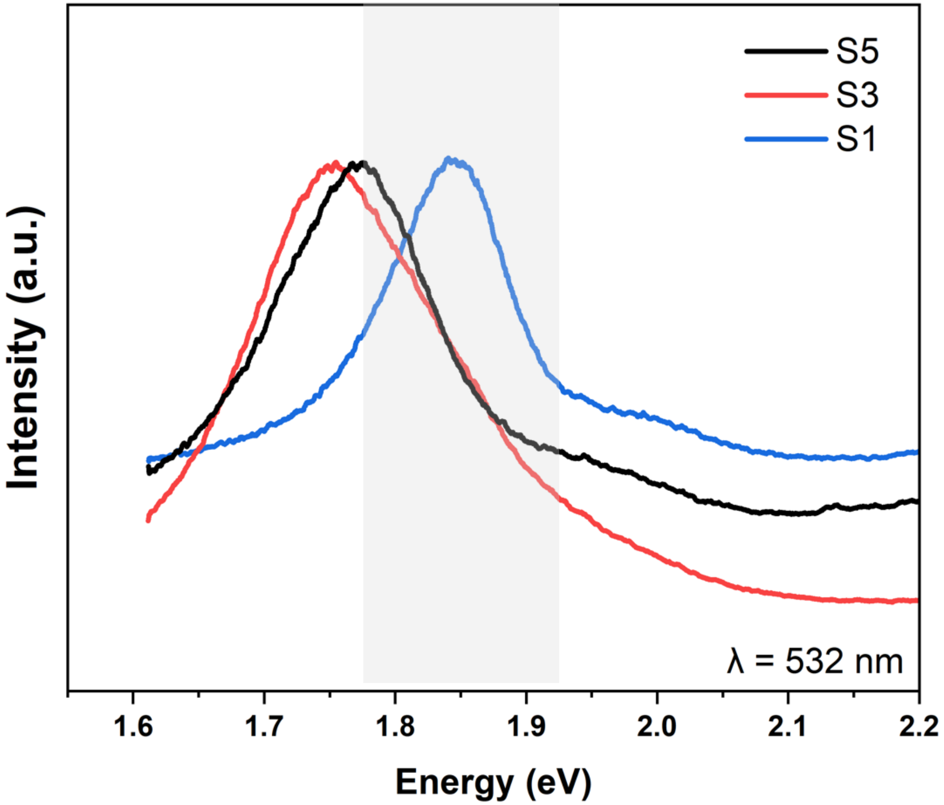


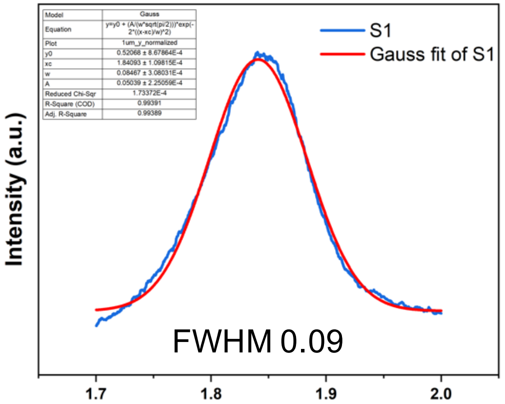
Point	E^1_{2g} (cm^{-1})	A_{1g} (cm^{-1})	Frequency difference (Δ)	Layers
1	386.5	405.3	20.8	2
2	383.5	408.4	24.9	> 3
3	383.5	405.3	21.9	3

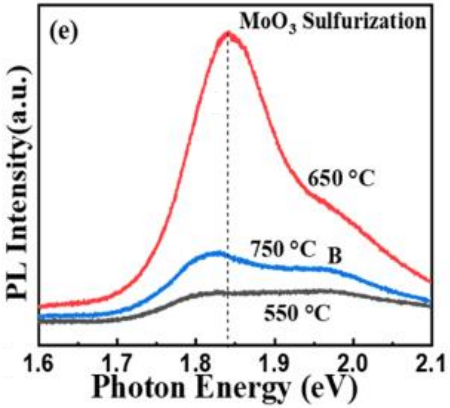
The Raman analysis verifies that the flakes consist of MoS_2, as indicated by the presence of characteristic peaks at 387cm^{-1} for E^1_{2g} and 407cm^{-1} for A_{1g}.

Material characterization - Photoluminescence spectroscopy





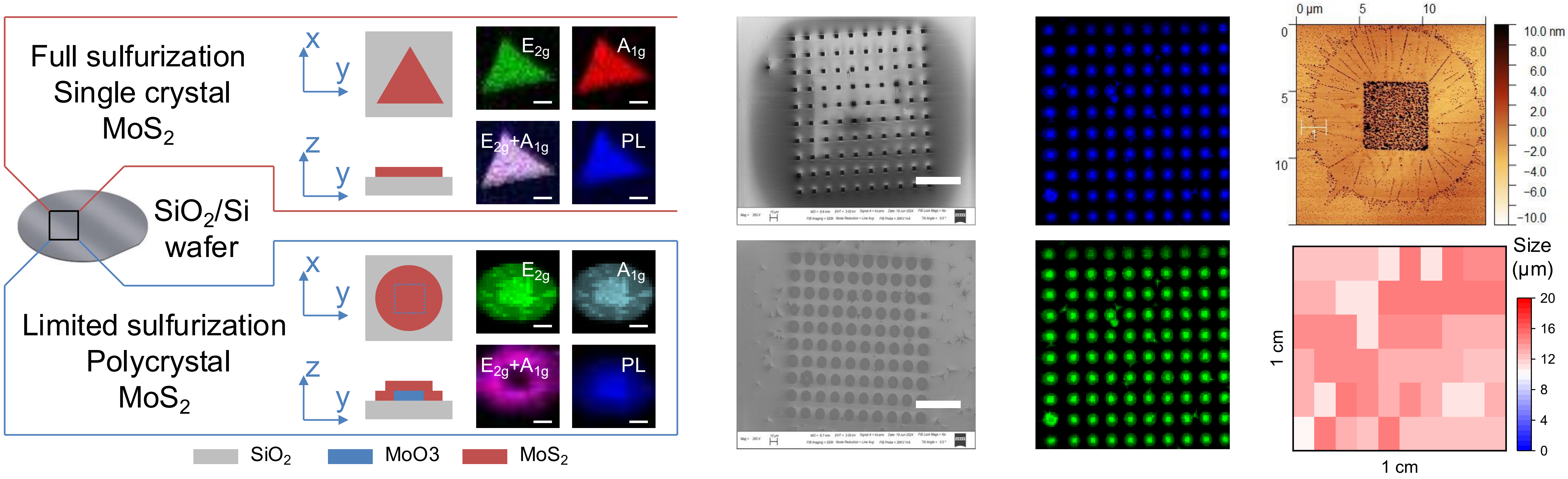




The photoluminescence (PL) spectrum of monolayer molybdenum disulfide (MoS_2) exhibits peaks in the range of approximately 1.85 eV to 2.00 eV. The S1 region displayed monolayer/bilayer (ML/BL) flakes, while the S3 and S5 regions showed multilayer flakes.

1. ACS Appl. Mater. Interfaces 2023, 15, 16308−16316

Material characterization - Array scale mapping



- The uniformity of the flakes can be assessed using 10 x 10 arrays through various characterization techniques such as SEM, AFM, Raman, and PL mapping.

Material characterization - Carrier transport measurement

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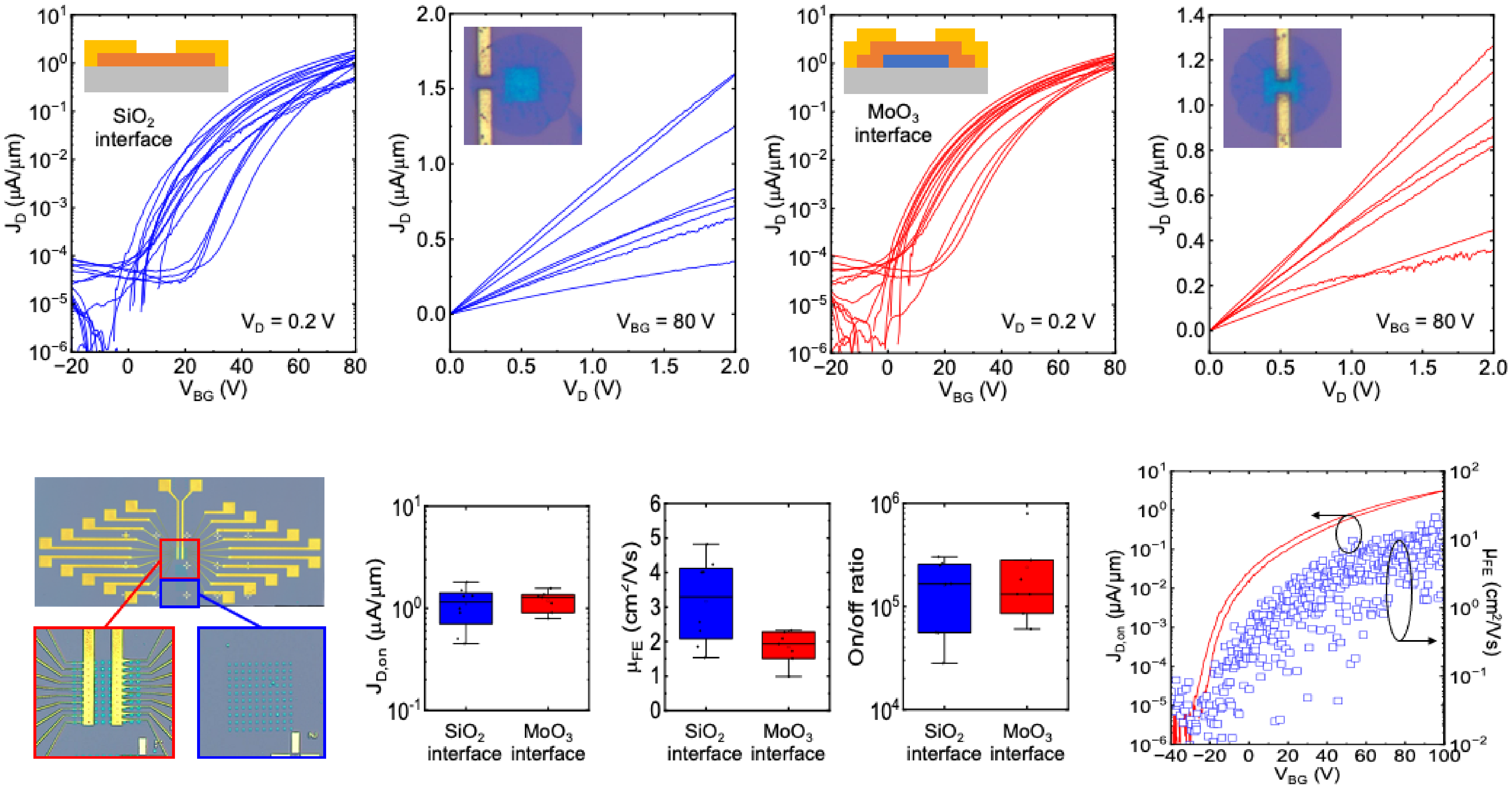
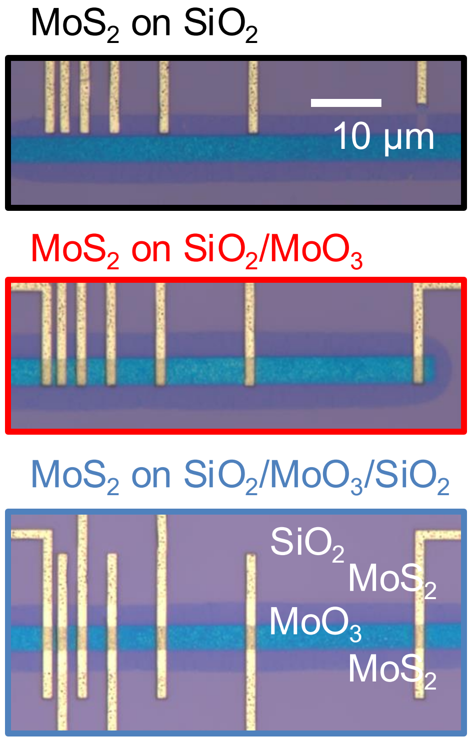
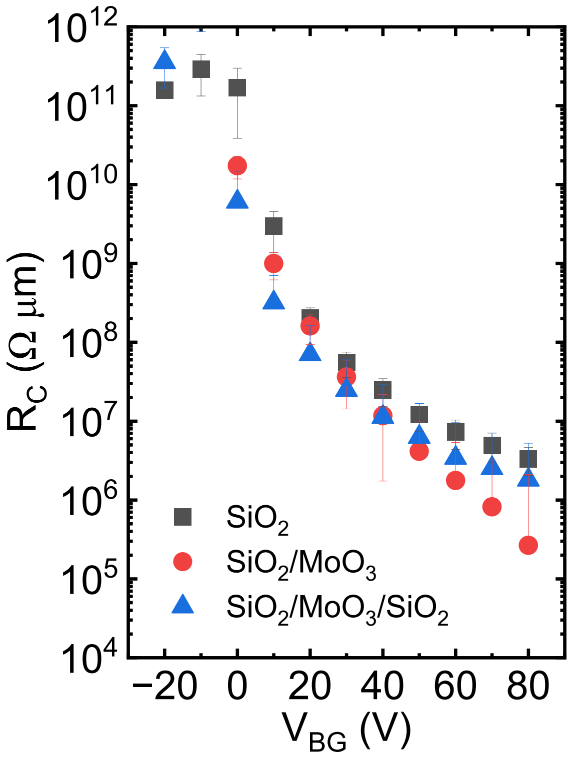
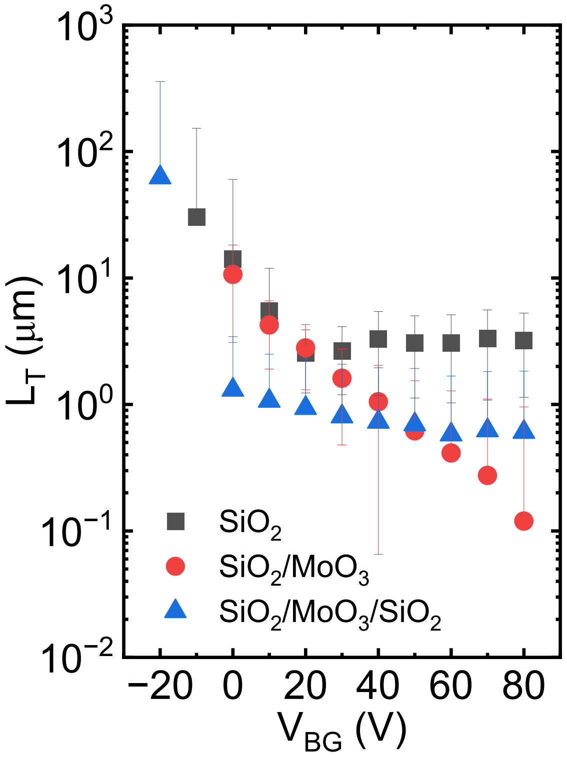


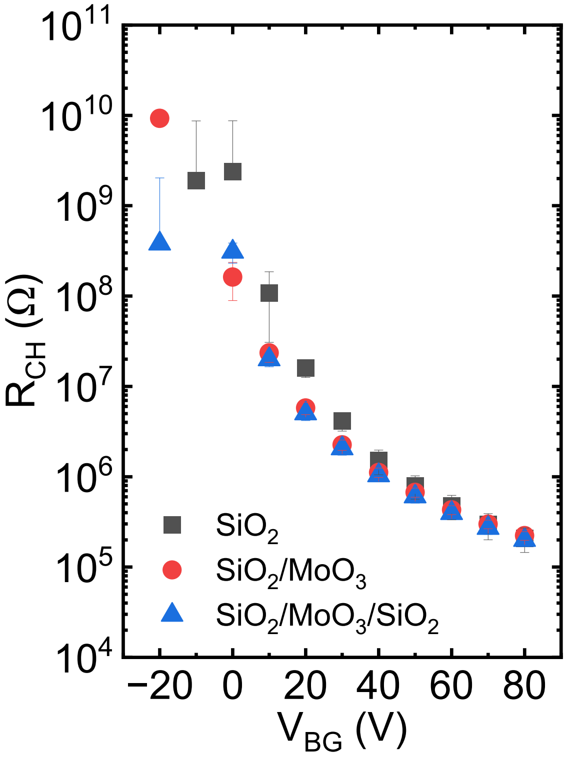
- A comparative investigation of MoS_2 FETs with MoO_3 and SiO_2 dielectric interfaces is performed, focusing on output and transfer characteristics (J_D-V_D and J_D-V_{BG}).
- Both FET types show linear J_D-V_D characteristics, indicating Ohmic contact.
- Optimized MoS_2 FET achieves $J_{D,on}$ of 3 µA/µm, μ_{FE} of 20 cm²/Vs, and on/off ratio up to 10^6.

Material characterization - Transmission line measurement





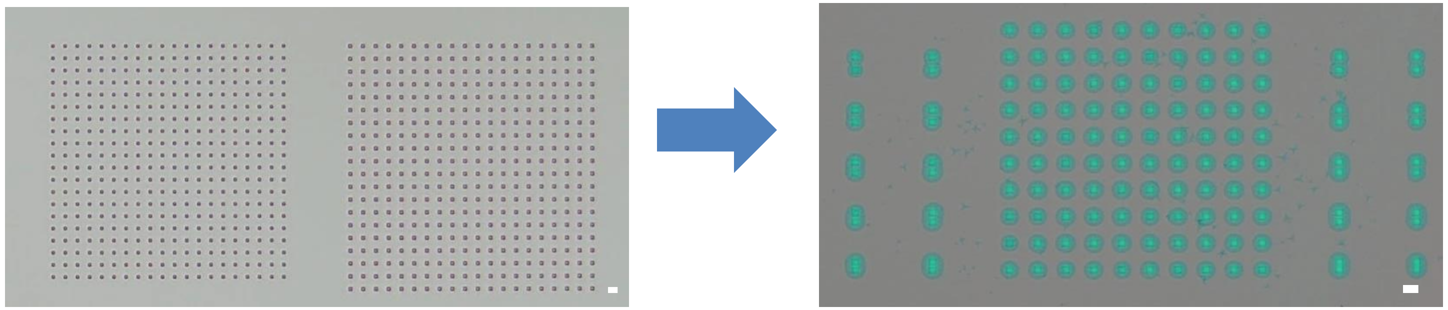




- Well-controlled growth enables defining the geometry of as-grown MoS_2 in arbitrary shapes. No need for lithography or etching processes.
- Created a long MoO_3 ribbon (5 µm × 200 µm) for Transmission Line Measurement (TLM).
- Greater involvement of the MoO_3 interface (compared to SiO_2) improves metal contact conditions. Lower contact resistance (R_c) and transfer length (T_L). Maintains the MoS_2 channel resistance (R_{CH}).

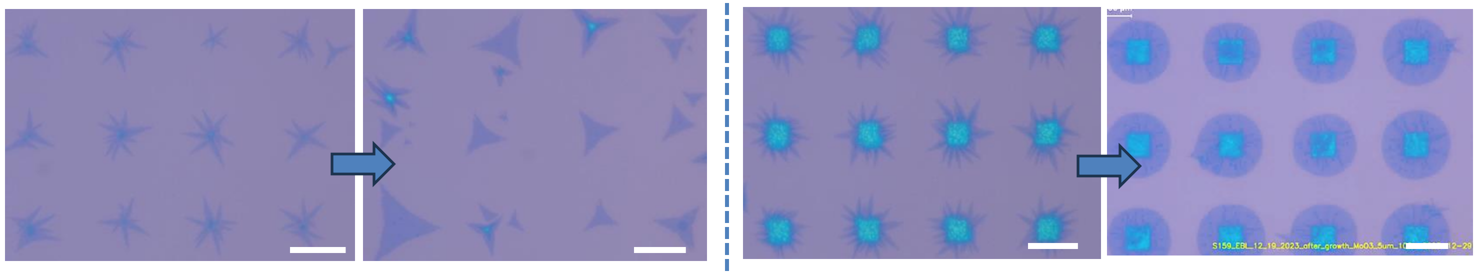
Research highlights

❑ Location-selective growth of MoS_2 on SiO_2 (scale bar: 10 μm)



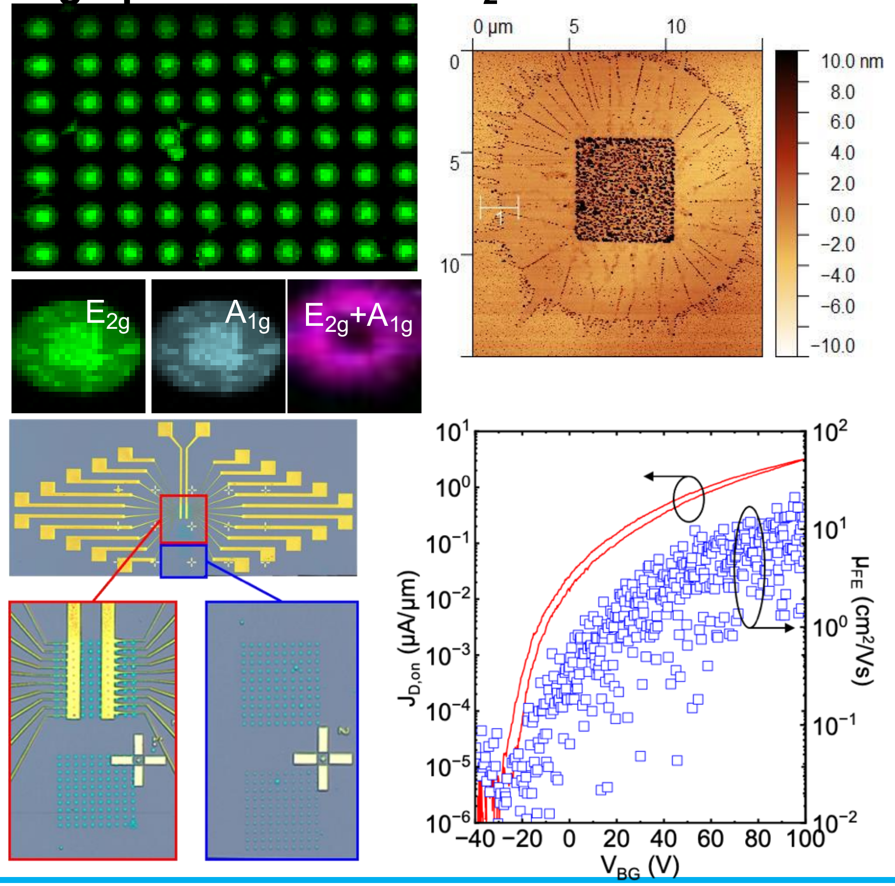
Patterned Mo precursor   CVD grown MoS_2 on SiO_2

❑ Controlled MoS_2 morphology evolution (scale bar: 10 μm)



Dendrite → Concaved triangle   Dendritic dot → Circular dot

❑ High performance MoS_2 transistors



Successfully demonstrate the selective CVD growth of 2D MoS_2 arrays directly on SiO_2 substrates with controlled morphologies and excellent electronic quality (~20 cm^2/Vs electron mobility).

Acknowledgement

Team members
- Nano Energy Technology Laboratory
- Emerging Nanoelectronics Research Group

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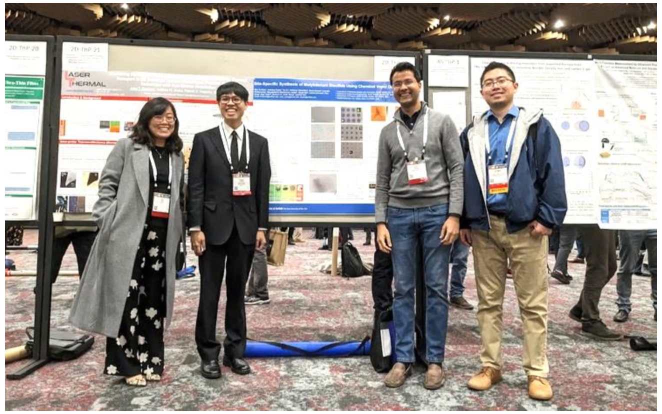

THANK YOU

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